

MMBT2907ALT1G

General Purpose Transistors

PNP Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-60	Vdc
Collector - Base Voltage	V_{CBO}	-60	Vdc
Emitter - Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-600	mAdc
Collector Current - Peak (Note 3)	I_{CM}	-1200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

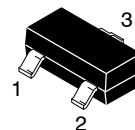
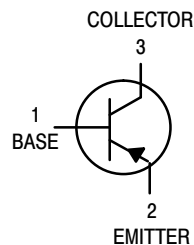
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
3. Reference SOA curve.



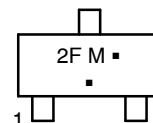
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236AB)
CASE 318
STYLE 6

MARKING DIAGRAM



2F = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2907ALT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT2907ALT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT2907ALT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (Note 4) (I _C = -1.0 mA, I _B = 0) (I _C = -10 mA, I _B = 0)	V _{(BR)CEO}	-60 -60	-	Vdc
Collector-Base Breakdown Voltage (I _C = -10 μA, I _E = 0)	V _{(BR)CBO}	-60	-	Vdc
Emitter-Base Breakdown Voltage (I _E = -10 μA, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _{CEX}	-	-50	nAdc
Collector Cutoff Current (V _{CB} = -50 Vdc, I _E = 0) (V _{CB} = -50 Vdc, I _E = 0, T _A = 125°C)	I _{CBO}	-	-0.010 -10	μAdc
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _{BL}	-	-50	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = -0.1 mA, V _{CE} = -10 Vdc) (I _C = -1.0 mA, V _{CE} = -10 Vdc) (I _C = -10 mA, V _{CE} = -10 Vdc) (I _C = -150 mA, V _{CE} = -10 Vdc) (I _C = -500 mA, V _{CE} = -10 Vdc) (Note 4)	h _{FE}	75 100 100 100 50	-	-
Collector-Emitter Saturation Voltage (Note 4) (I _C = -150 mA, I _B = -15 mA) (Note 4) (I _C = -500 mA, I _B = -50 mA)	V _{CE(sat)}	-	-0.4 -1.6	Vdc
Base-Emitter Saturation Voltage (Note 4) (I _C = -150 mA, I _B = -15 mA) (I _C = -500 mA, I _B = -50 mA)	V _{BE(sat)}	-	-1.3 -2.6	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (Notes 4, 5), (I _C = -50 mA, V _{CE} = -20 Vdc, f = 100 MHz)	f _T	200	-	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	30	pF

SWITCHING CHARACTERISTICS

Turn-On Time	(V _{CC} = -30 Vdc, I _C = -150 mA, I _{B1} = -15 mA)	t _{on}	-	45	ns
Delay Time		t _d	-	10	
Rise Time		t _r	-	40	
Turn-Off Time	(V _{CC} = -6.0 Vdc, I _C = -150 mA, I _{B1} = I _{B2} = -15 mA)	t _{off}	-	100	
Storage Time		t _s	-	80	
Fall Time		t _f	-	30	

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
- f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

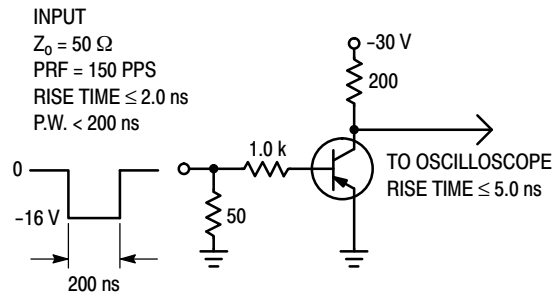


Figure 1. Delay and Rise Time Test Circuit

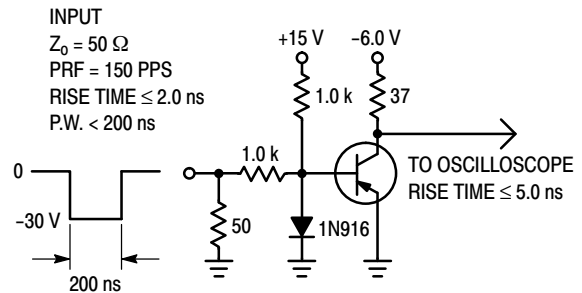


Figure 2. Storage and Fall Time Test Circuit

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TYPICAL CHARACTERISTICS

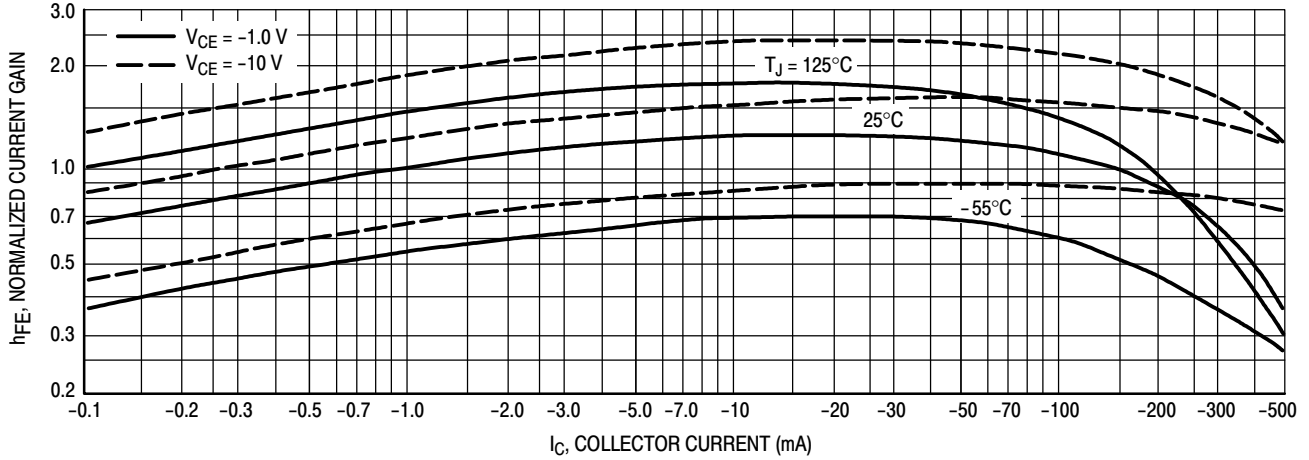


Figure 3. DC Current Gain

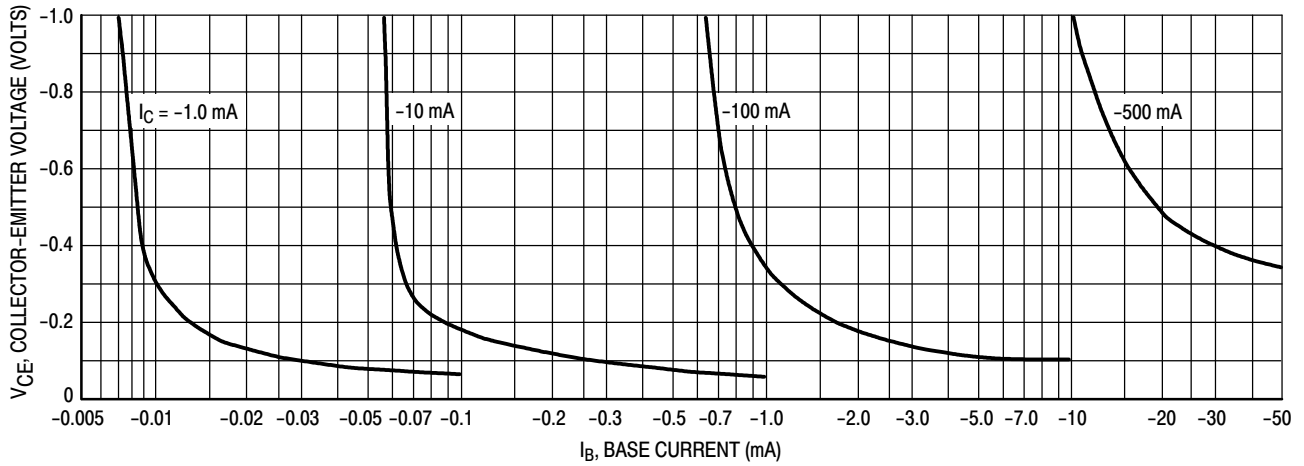


Figure 4. Collector Saturation Region

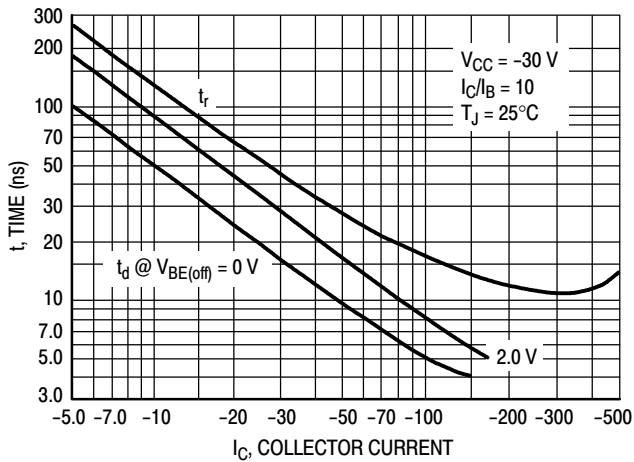


Figure 5. Turn-On Time

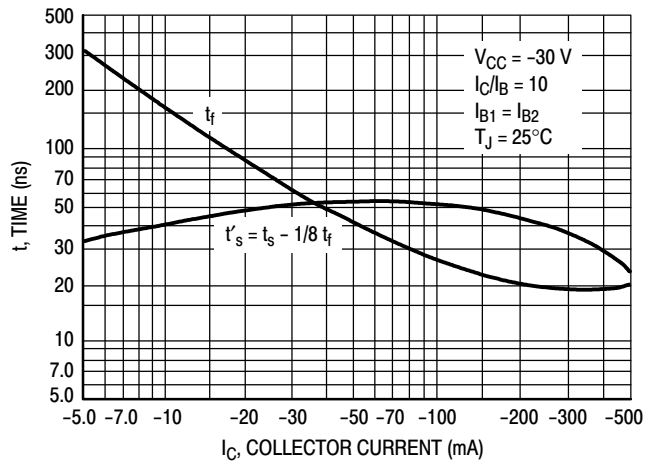


Figure 6. Turn-Off Time

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TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

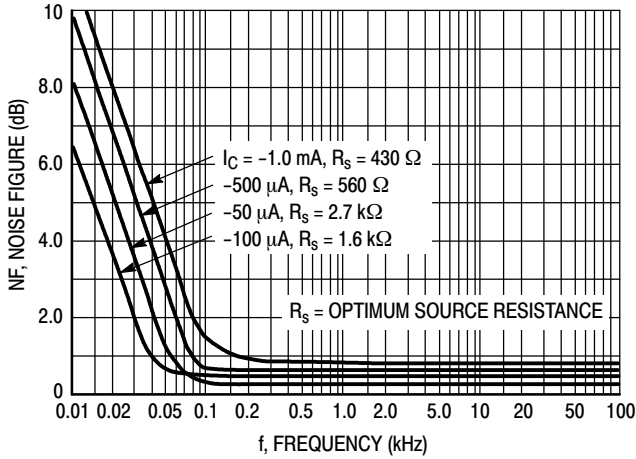


Figure 7. Frequency Effects

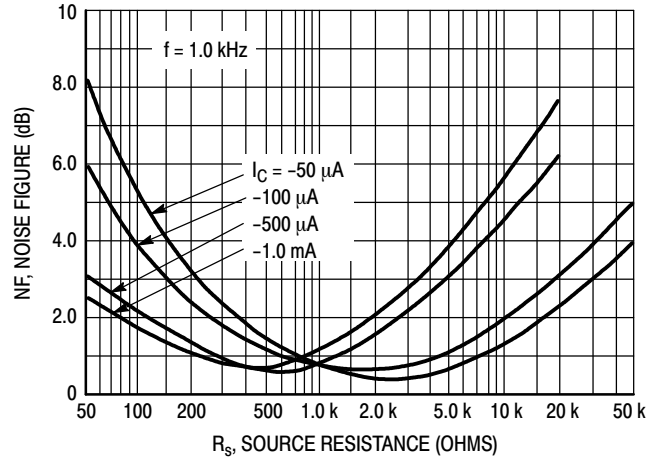


Figure 8. Source Resistance Effects

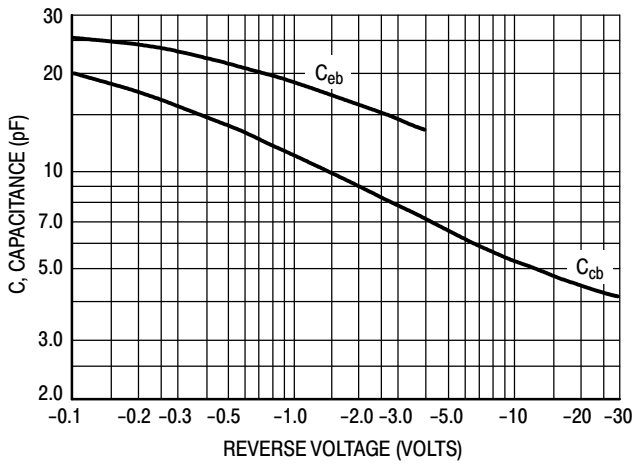


Figure 9. Capacitances

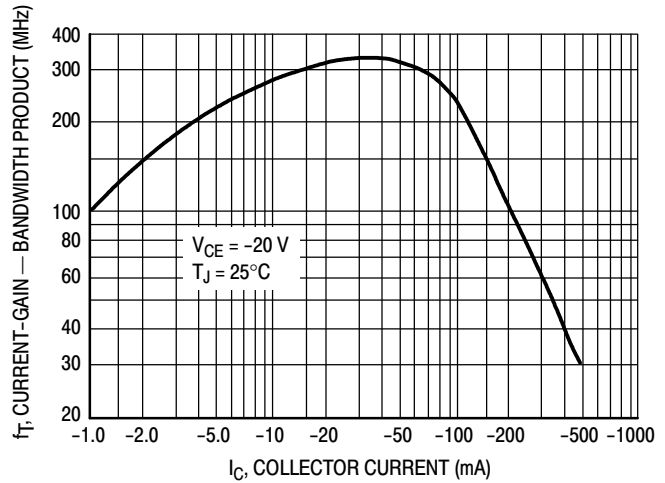


Figure 10. Current-Gain - Bandwidth Product

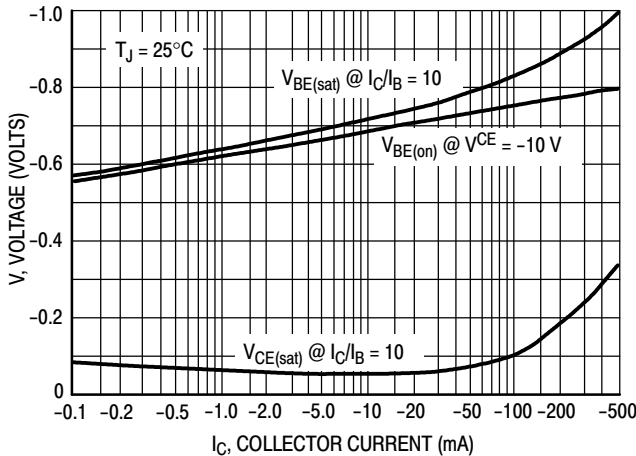


Figure 11. "On" Voltage

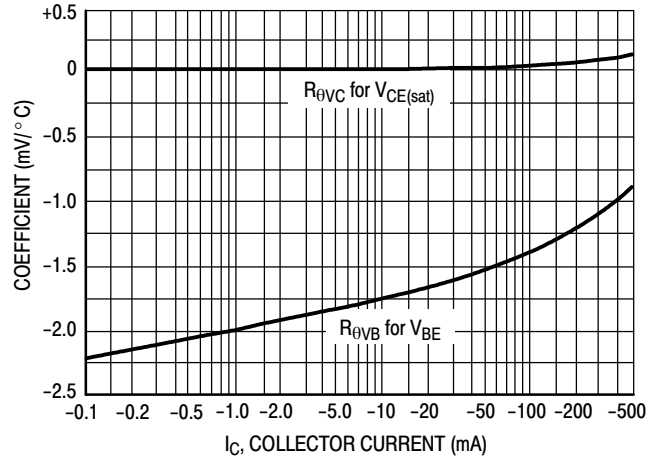


Figure 12. Temperature Coefficients

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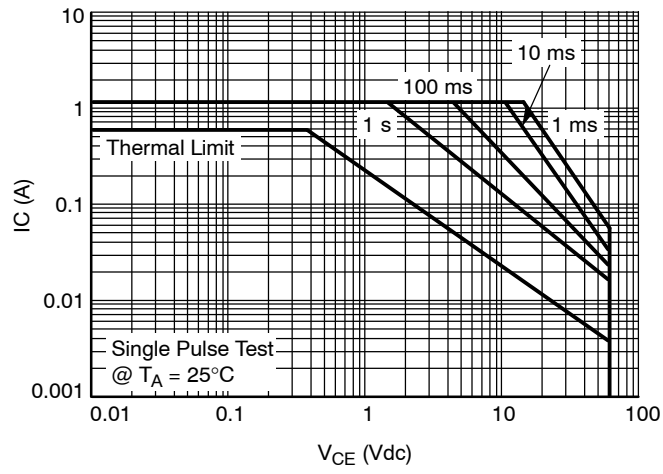
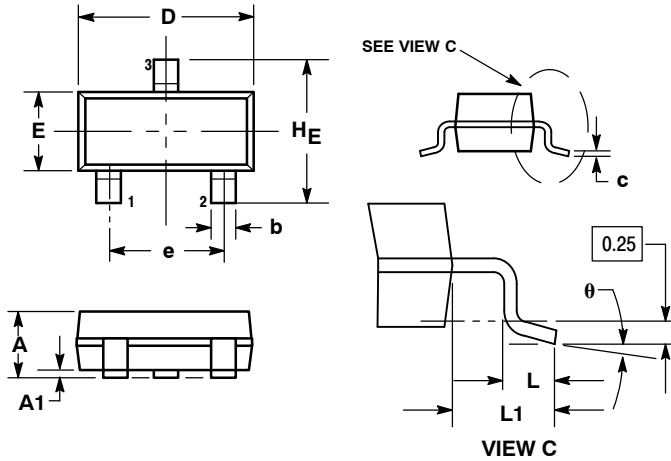


Figure 13. Safe Operating Area

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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

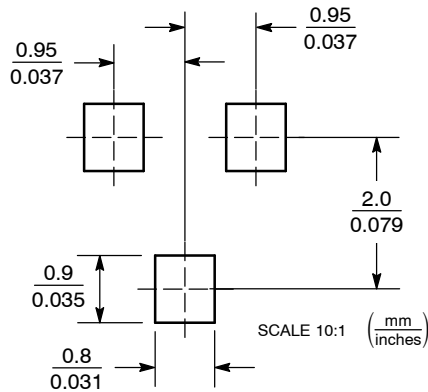
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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